

connecting the chip and the lead layer; and a molded resin covering the chip, conductive elements, solder masks, lead layer and die pad layer.

32(New). The semiconductor package of claim 31, wherein the solder mask is made from photosensitive and insulative materials selected from the group consisting of polyimide and ultraviolet-curable resins.

33(New). The semiconductor package of claim 32, wherein the lead layer and die pad layer are made of conductive materials selected from the group consisting of nickel and gold.

34(New). The semiconductor package of claim 32, wherein the solder mask is formed by performing photolithography process on a polyimide or ultraviolet-curable resin layer.

35(New). The semiconductor package of claim 31, wherein the lead layer and die pad layer are formed by plating.

36(New). The semiconductor package of claim 31, wherein the conductive elements are made of a material selected from the group consisting of gold, copper and aluminum.

37(New). The semiconductor package of claim 31, wherein the die pad layer is replaced by a solder mask.

38(New). A single semiconductor package consisting essentially of an unsupported single layer linearly consisting essentially of at least two solder mask portions formed at selected locations, and between and adjacent said solder mask portions is a die pad portion of said layer contiguous to each solder mask portion; and lead portions of said layer adjacent to and contiguous to said solder mask portions, said die pad has a chip adhering by a silver paste to the die pad surface; a plurality of

conductive elements are electrically connecting the chip and the lead layer; and a molded resin covering the chip, conductive elements, solder masks, lead layer and die pad layer.

39(New). The semiconductor package of claim 38, wherein the solder mask is made from photosensitive and insulative materials selected from the group consisting of polyimide and ultraviolet-curable resins.

40(New). The semiconductor package of claim 38, wherein the lead layer and die pad layer are made of conductive materials selected from the group consisting of nickel and gold.

41(New). The semiconductor package of claim 38, wherein the solder mask is formed by performing photolithography process on a polyimide or ultraviolet-curable resin layer.

42(New). The semiconductor package of claim 38, wherein the lead layer and die pad layer are formed by plating.

43(New). The semiconductor package of claim 38, wherein the conductive elements are made of a material selected from the group consisting of gold, copper and aluminum.

44(New). The semiconductor package of claim 38, wherein the die pad layer is replaced by a solder mask.